

AMENDMENT

Please make the following amendments:

IN THE CLAIMS:

Please amend claims 7, 8, 16, and 17 as follows:

A1
7. (Amended) The method of claim 1, wherein implanting dopant atoms into said gate electrode layer to define a layer of dopant material in said gate electrode layer comprises implanting dopant atoms into said gate electrode layer to define a layer of dopant material in said gate electrode layer, said layer of dopant material being completely separate from said gate dielectric layer.

A2
8. (Amended) The method of claim 1, wherein implanting dopant atoms into said gate electrode layer to define a layer of dopant material in said gate electrode layer comprises implanting dopant atoms into said gate electrode layer to define a layer of dopant material in said gate electrode layer, said layer of dopant material defining a region of said gate electrode layer that is positioned between said layer of dopant material and said gate dielectric layer.

A2
16. (Amended) The method of claim 14, wherein implanting dopant atoms into said gate electrode layer to define a layer of dopant material in said gate electrode layer comprises implanting dopant atoms into said gate electrode layer to define a layer of dopant material in said gate electrode layer, said layer of dopant material being completely separate from said gate dielectric layer.